

## HMC372LP3 / 372LP3E

v03.0610



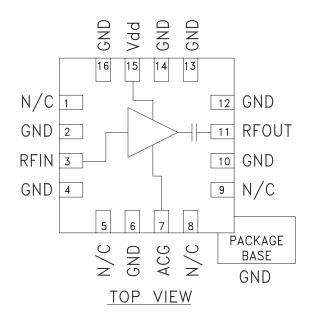
## GaAs PHEMT MMIC LOW NOISE AMPLIFIER, 700 - 1000 MHz

#### Typical Applications

The HMC372LP3 / HMC372LP3E is ideal for basestation receivers:

- · GSM, GPRS & EDGE
- CDMA & W-CDMA
- · Private Land Mobile Radio

#### **Functional Diagram**



#### **Features**

Noise Figure: < 1 dB Output IP3: +34 dBm

Gain: 15 dB

Very Stable Gain vs. Supply & Temperature

Single Supply: +5V @ 100 mA

50 Ohm Matched Output

#### General Description

The HMC372LP3 & HMC372LP3E are GaAs PHEMT MMIC Low Noise Amplifiers that are ideal for GSM & CDMA cellular basestation front-end receivers operating between 700 and 1000 MHz. The amplifier has been optimized to provide 1 dB noise figure, 15 dB gain and +34 dBm output IP3 from a single supply of +5V @ 100 mA. Input and output return losses are 25 and 14 dB respectively with the LNA requiring only four external components to optimize the RF Input match, RF ground and DC bias. For applications which require improved noise figure, please see the HMC617LP3(E).

## Electrical Specifications, $T_{\Delta} = +25^{\circ}$ C, Vs = +5V

Parameter	Min.	Тур.	Max.	Min.	Тур.	Max.	Units
Frequency Range		810 - 960 700 - 1000			MHz		
Gain	12.5	14.5		11.5	14.5		dB
Gain Variation Over Temperature		0.008	0.015		0.008	0.015	dB / °C
Noise Figure		1.0	1.3		1.0	1.3	dB
Input Return Loss		25			25		dB
Output Return Loss		14			12		dB
Reverse Isolation		20			22		dB
Output Power for 1dB Compression (P1dB)	18	21		17	20		dBm
Saturated Output Power (Psat)		23.5			22.5		dBm
Output Third Order Intercept (IP3) (-20 dBm Input Power per tone, 1 MHz tone spacing)		34		30	33		dBm
Supply Current (Idd)		100			100		mA

# HMC372\* PRODUCT PAGE QUICK LINKS

Last Content Update: 02/23/2017

## COMPARABLE PARTS 🖳

View a parametric search of comparable parts.

## **EVALUATION KITS**

· HMC372LP3 Evaluation Board.

## **DOCUMENTATION**

#### **Application Notes**

- AN-1363: Meeting Biasing Requirements of Externally Biased RF/Microwave Amplifiers with Active Bias Controllers
- Broadband Biasing of Amplifiers General Application Note
- MMIC Amplifier Biasing Procedure Application Note
- Thermal Management for Surface Mount Components General Application Note

#### **Data Sheet**

HMC372 Data Sheet

### **TOOLS AND SIMULATIONS**

HMC372 S-Parameter

## REFERENCE MATERIALS 🖵

#### **Quality Documentation**

- Package/Assembly Qualification Test Report: 16L 3x3mm QFN Package (QTR: 11003 REV: 02)
- Package/Assembly Qualification Test Report: LP2, LP2C, LP3, LP3B, LP3C, LP3D, LP3F, LP3G (QTR: 2014-0364)
- Package/Assembly Qualification Test Report: Plastic Encapsulated QFN (QTR: 05006 REV: 02)
- Semiconductor Qualification Test Report: PHEMT-B (QTR: 2013-00233)

#### **Technical Articles**

• Active Multipliers & Dividers to Simplify Synthesizers

#### DESIGN RESOURCES 🖳

- HMC372 Material Declaration
- PCN-PDN Information
- · Quality And Reliability
- · Symbols and Footprints

## **DISCUSSIONS**

View all HMC372 EngineerZone Discussions.

## SAMPLE AND BUY 🖳

Visit the product page to see pricing options.

## TECHNICAL SUPPORT 🖳

Submit a technical question or find your regional support number.

## DOCUMENT FEEDBACK 🖵

Submit feedback for this data sheet.

AMPLIFIER, 700 - 1000 MHz

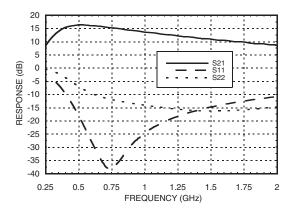
GaAs PHEMT MMIC LOW NOISE



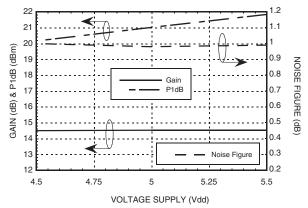
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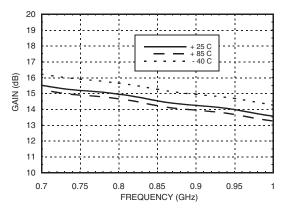
#### **Broadband Gain & Return Loss**



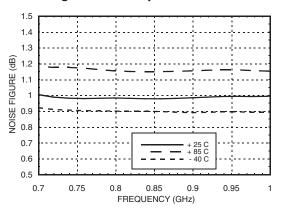
# Gain, Noise Figure & Power vs. Supply Voltage @ 850MHz



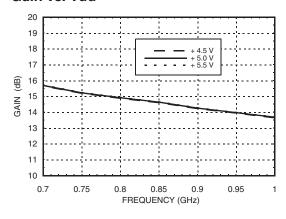
#### Gain vs. Temperature



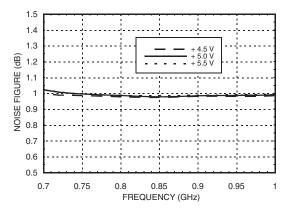
#### Noise Figure vs. Temperature



#### Gain vs. Vdd



#### Noise Figure vs. Vdd

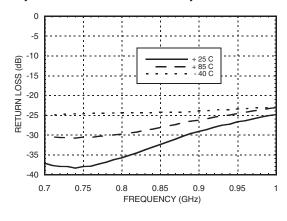




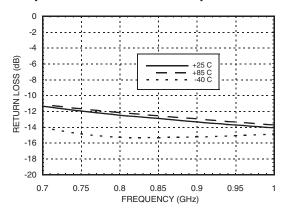


## GaAs PHEMT MMIC LOW NOISE AMPLIFIER, 700 - 1000 MHz

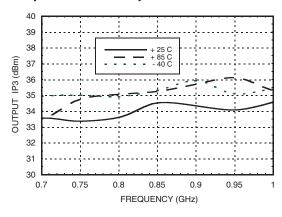
#### Input Return Loss vs. Temperature



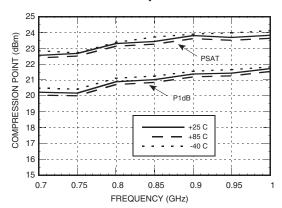
#### **Output Return Loss vs. Temperature**



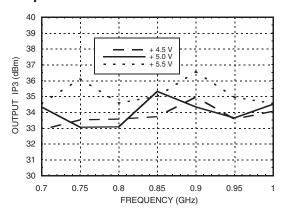
#### Output IP3 vs. Temperature



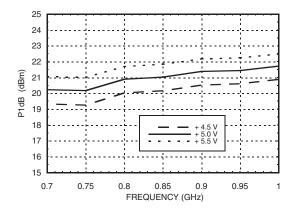
#### P1dB & Psat vs. Temperature



#### Output IP3 vs. Vdd



#### P1dB vs. Vdd

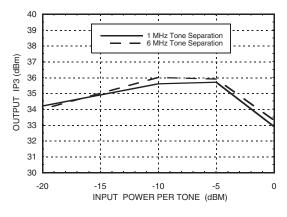




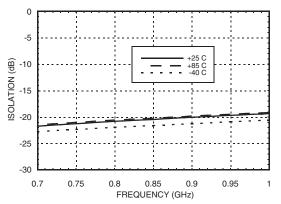


## GaAs PHEMT MMIC LOW NOISE AMPLIFIER, 700 - 1000 MHz

### Output IP3 vs. Input Power @ 950 MHz



### Reverse Isolation vs. Temperature



#### **Absolute Maximum Ratings**

Drain Bias Voltage (Vdd)	+8.0 Vdc
RF Input Power (RFIN)(Vs = +5.0 Vdc)	+15 dBm
Channel Temperature	150 °C
Continuous Pdiss (T = 85 °C) (derate 15.6 mW/°C above 85 °C)	1.015 W
Thermal Resistance (channel to ground paddle)	64.1 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C

### Typical Supply Current vs. Vdd

Vdd (Vdc)	Idd (mA)		
+4.5	98		
+5.0	100		
+5.5	102		



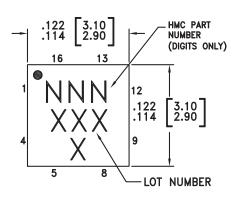
ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

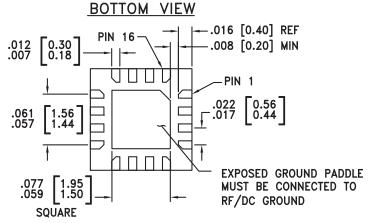


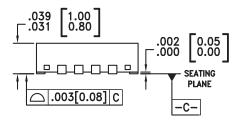


## GaAs PHEMT MMIC LOW NOISE AMPLIFIER, 700 - 1000 MHz

#### **Outline Drawing**







#### NOTES:

- 1. LEADFRAME MATERIAL: COPPER ALLOY
- 2. DIMENSIONS ARE IN INCHES [MILLIMETERS]
- 3. LEAD SPACING TOLERANCE IS NON-CUMULATIVE
- 4. PAD BURR LENGTH SHALL BE 0.15mm MAXIMUM. PAD BURR HEIGHT SHALL BE 0.05mm MAXIMUM.
- 5. PACKAGE WARP SHALL NOT EXCEED 0.05mm.
- 6. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.
- 7. REFER TO HITTITE APPLICATION NOTE FOR SUGGESTED LAND PATTERN.

### Package Information

Part Number	Package Body Material Lead Finish		MSL Rating	Package Marking [3]	
HMC372LP3	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 [1]	H372 XXXX	
HMC372LP3E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 [2]	H372 XXXX	

- [1] Max peak reflow temperature of 235 °C
- [2] Max peak reflow temperature of 260 °C
- [3] 4-Digit lot number XXXX



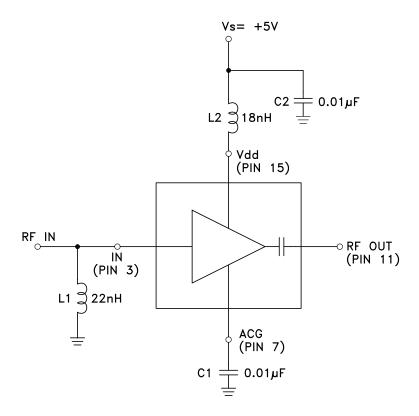


## GaAs PHEMT MMIC LOW NOISE AMPLIFIER, 700 - 1000 MHz

#### **Pin Descriptions**

Pin Number	Function	Description	Interface Schematic
1, 5, 8, 9	N/C	No connection necessary. These pins may be connected to RF/DC ground.	
2, 4, 6, 10, 12, 13, 14, 16	GND	These pins must be connected to RF/DC ground.	○ GND =
3	RF IN	This pin is matched to 50 Ohms with a 22 nH inductor to ground. See Application Circuit.	RFIN O
7, 15	ACG	AC Ground - An external capacitor of 0.01µF to ground is required for low frequency bypassing.  See Application Circuit for further details.	O Vdd
	I Vaa I	Power supply voltage. Choke inductor and bypass capacitor are required. See application circuit.	ACG \\ \frac{\}{\}
11	RF OUT	This pin is AC coupled and matched to 50 Ohms.	— —ORFOUT

## **Application Circuit**



Note 1: Choose value of capacitor C1 for low frequency bypassing. A 0.01  $\mu$ F  $\pm$ 10% capacitor is recommended. Note 2: L1, L2 and C1 should be located as close to the pins as possible.

AMPLIFIER, 700 - 1000 MHz

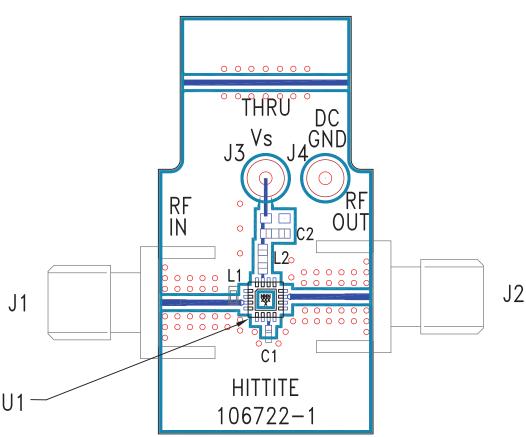


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#### **Evaluation PCB**

# GaAs PHEMT MMIC LOW NOISE



#### List of Materials for Evaluation PCB 106821 [1]

Item	Description	
J1 - J2	PCB Mount SMA RF Connector	
J3 - J4	DC Pin	
C1	10000 pF Capacitor, 0402 Pkg.	
C2	10000 pF Capacitor, 0060 Pkg.	
L1	22nH Inductor, 0402 Pkg.	
L2	18nH Inductor, 0603 Pkg.	
U1	HMC372LP3 / HMC372LP3E Amplifier	
PCB [2]	106722 Evaluation PCB	

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation circuit board shown is available from Hittite upon request.



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Notes:

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